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(71) Applicant: **NEWPORT FAB, LLC DBA JAZZ SEMI-CONDUCTOR** [US/US]; 4321 Jamboree Road, Newport Beach, CA 92660 (US).

(72) Inventors: **KALBURGE, Amol**; 4371 Rafael Street, Irvine, CA 92604 (US). **YIN, Kevin, Q.**; 28 Santa Cruz Aisle, Irvine, CA 92606 (US).

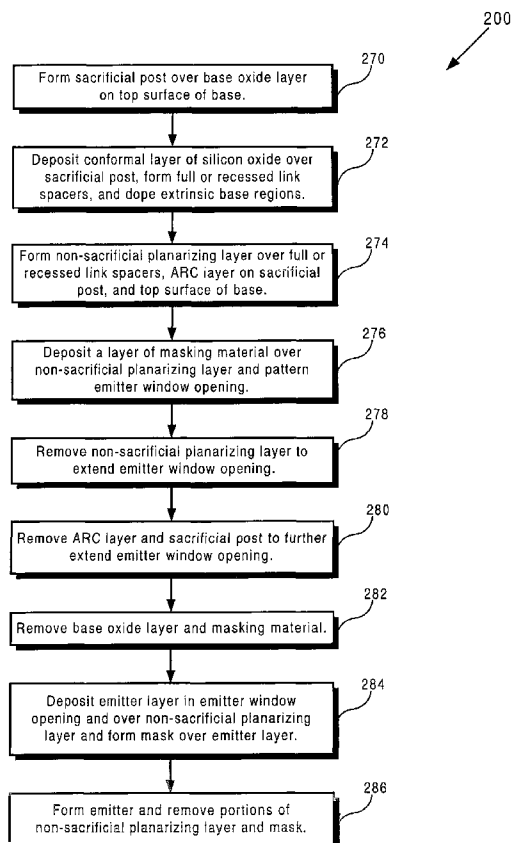
(74) Agent: **FARJAMI, Michael**; Farjami & Farjami LLP, 26522 La Alameda Ave., Suite 360, Mission Viejo, CA 92691 (US).

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(54) Title: METHOD FOR FABRICATING A SELF-ALIGNED BIPOLAR TRANSISTOR WITH PLANARIZING LAYER AND RELATED STRUCTURE



(57) Abstract: According to one exemplary embodiment, a bipolar transistor comprises a base having a top surface. The bipolar transistor further comprises first and second link spacers situated on the top surface of the base. The bipolar transistor further comprises a sacrificial post situated on the top surface of the base between the first and second link spacers. The first and second link spacers may have a height, for example, approximately equal to or, in another embodiment, substantially less than a height of the sacrificial post. According to this exemplary embodiment, the bipolar transistor further comprises a non-sacrificial planarizing layer situated over the sacrificial post, first and second link spacers, and base. The non-sacrificial planarizing layer may comprise, for example, silicate glass. The sacrificial planarizing layer may have a height, for example, approximately equal to or, in another embodiment, greater than greater than a height of the first and second link spacers.

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